

SK75GB12T4T



SEMITOP® 3

IGBT Module

SK75GB12T4 T

Target Data

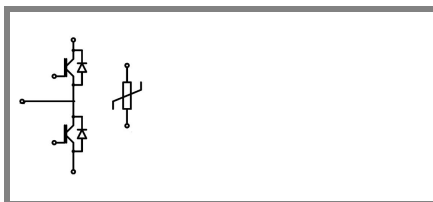
Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{CE,sat}$, V_F = chip level value

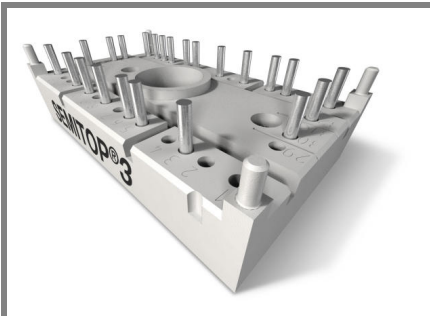


GB-T

| Absolute Maximum Ratings | | $T_s = 25\text{ °C}$, unless otherwise specified | | |
|--------------------------|----------------------------------------------------------------------------------------------------------|---------------------------------------------------|----|-------|
| Symbol | Conditions | Values | | Units |
| IGBT | | | | |
| V_{CES} | $T_j = 25\text{ °C}$ | 1200 | | V |
| I_C | $T_j = 175\text{ °C}$ | $T_s = 25\text{ °C}$ | 80 | A |
| | | $T_s = 70\text{ °C}$ | 65 | A |
| I_{CRM} | $I_{CRM} = 3 \times I_{Cnom}$ | 225 | | A |
| V_{GES} | | ± 20 | | V |
| t_{psc} | $V_{CC} = 800\text{ V}$; $V_{GE} \leq 15\text{ V}$; $T_j = 150\text{ °C}$ $V_{CES} < 1200\text{ V}$ | 10 | | µs |
| Inverse Diode | | | | |
| I_F | $T_j = 175\text{ °C}$ | $T_s = 25\text{ °C}$ | 70 | A |
| | | $T_s = 70\text{ °C}$ | 55 | A |
| I_{FRM} | $I_{FRM} = 3 \times I_{Fnom}$ | 225 | | A |
| I_{FSM} | $t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$ | 425 | | A |
| Module | | | | |
| $I_{t(RMS)}$ | | | | A |
| T_{vj} | | -40 ... +175 | | °C |
| T_{stg} | | -40 ... +125 | | °C |
| V_{isol} | AC, 1 min. | 2500 | | V |

| Characteristics | | $T_s = 25\text{ °C}$, unless otherwise specified | | | |
|-----------------|-------------------------------------------------------|---------------------------------------------------|-------|------|-------|
| Symbol | Conditions | min. | typ. | max. | Units |
| IGBT | | | | | |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C = 3\text{ mA}$ | 5 | 5,8 | 6,5 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$ | $T_j = 25\text{ °C}$ | 0,01 | | mA |
| | | $T_j = 125\text{ °C}$ | | | mA |
| I_{GES} | $V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$ | $T_j = 25\text{ °C}$ | 600 | | nA |
| | | $T_j = 125\text{ °C}$ | | | nA |
| V_{CE0} | | $T_j = 25\text{ °C}$ | 1,1 | 1,3 | V |
| | | $T_j = 150\text{ °C}$ | 1 | 1,2 | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ | $T_j = 25\text{ °C}$ | 10 | | mΩ |
| | | $T_j = 150\text{ °C}$ | 16 | | mΩ |
| $V_{CE(sat)}$ | $I_{Cnom} = 75\text{ A}$, $V_{GE} = 15\text{ V}$ | $T_j = 25\text{ °C}_{chiplev.}$ | 1,85 | 2,05 | V |
| | | $T_j = 150\text{ °C}_{chiplev.}$ | 2,25 | 2,45 | V |
| C_{ies} | $V_{CE} = 25$, $V_{GE} = 0\text{ V}$ | $f = 1\text{ MHz}$ | 4,4 | | nF |
| C_{oes} | | | 0,29 | | nF |
| C_{res} | | | 0,235 | | nF |
| Q_G | $V_{GE} = -7V...+15V$ | 570 | | nC | |
| R_{Gint} | $T_j = 25\text{ °C}$ | 10 | | Ω | |
| $t_{d(on)}$ | $R_{Gon} = 24\text{ Ω}$ $di/dt = 1360\text{ A/μs}$ | $V_{CC} = 600V$ $I_C = 75A$ | 63 | | ns |
| t_r | | | 65 | | ns |
| E_{on} | | | 13,6 | mJ | |
| $t_{d(off)}$ | $R_{Goff} = 24\text{ Ω}$ | $T_j = 150\text{ °C}$ $V_{GE} = -7/+15V$ | 521 | | ns |
| | | | 80 | ns | |
| E_{off} | | | 8,2 | | mJ |
| $R_{th(j-s)}$ | per IGBT | 0,74 | | K/W | |

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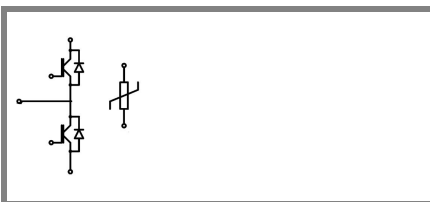
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Typical Applications*

Remarks

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| Characteristics | | | min. | typ. | max. | Units |
|---------------------------|----------------------------------------------------------|-----------------------------------------------|------|--------------|------|---------------|
| Symbol | Conditions | | | | | |
| Inverse Diode | | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom} = 75 \text{ A}; V_{GE} = 0 \text{ V}$ | $T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$ | | 2,1 | 2,5 | V |
| | | $T_j = 150 \text{ }^\circ\text{C}_{chiplev.}$ | | 2,4 | 2,5 | V |
| V_{F0} | | $T_j = 25 \text{ }^\circ\text{C}$ | | 1,3 | 1,5 | V |
| | | $T_j = 150 \text{ }^\circ\text{C}$ | | 0,9 | 1,1 | V |
| r_F | | $T_j = 25 \text{ }^\circ\text{C}$ | | 12 | 13,3 | m Ω |
| | | $T_j = 150 \text{ }^\circ\text{C}$ | | 16 | 17,3 | m Ω |
| I_{RRM} | $I_F = 75 \text{ A}$ | $T_j = 150 \text{ }^\circ\text{C}$ | | 41 | | A |
| Q_{rr} | $di/dt = 1360 \text{ A}/\mu\text{s}$ | | | 10,6 | | μC |
| E_{rr} | $V_{CC} = 600\text{V}$ | | | 3,39 | | mJ |
| $R_{th(j-s)D}$ | per diode | | | 0,97 | | K/W |
| M_s | to heat sink | | | | 2,5 | Nm |
| w | | | | 30 | | g |
| Temperature sensor | | | | | | |
| R_{100} | $T_s = 100^\circ\text{C}$ ($R_{25} = 5\text{k}\Omega$) | | | 493 \pm 5% | | Ω |

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

